

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L26	158215	(etch\$1 remov\$3) near5 (oxide dioxide barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 09:59
L27	4988	26 same dielectric with (opening\$1 hole\$1 trench\$2 via\$1 recess\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 10:00
L28	158	27 same (silicon-near2 carbide SiC)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 10:02

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L1	158215	(etch\$1 remov\$3) near5 (oxide dioxide barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 13:12
L2	4988	1 same dielectric with (opening\$1 hole\$1 trench\$2 via\$1 recess\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 13:14
L3	126	2 same ((poly amorphous) adj silicon refractory adj metal\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 13:15
L4	90	3 and (sidewall\$1 spacer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 13:15